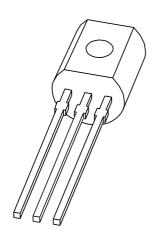
### **DISCRETE SEMICONDUCTORS**

# DATA SHEET



## BC617; BC618 NPN Darlington transistors

Product specification Supersedes data of September 1994 File under Discrete Semiconductors, SC04 1997 Jul 04





### **NPN Darlington transistors**

BC617; BC618

### **FEATURES**

- Low current (max. 500 mA)
- Low voltage (max. 55 V)
- High DC current gain.

### **APPLICATIONS**

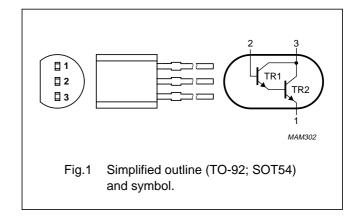
- General purpose low frequency
- · Relay drivers.

### **DESCRIPTION**

NPN Darlington transistor in a TO-92; SOT54 plastic package.

#### **PINNING**

PIN	DESCRIPTION
1	emitter
2	base
3	collector



#### **QUICK REFERENCE DATA**

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter			
	BC617		_	50	V
	BC618		_	80	V
V <sub>CES</sub>	collector-emitter voltage	V <sub>BE</sub> = 0			
	BC617		_	40	V
	BC618		_	55	V
I <sub>C</sub>	collector current		_	1	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	_	500	mW
h <sub>FE</sub>	DC current gain	$I_C = 1 \text{ mA}; V_{CE} = 5 \text{ V}$			
	BC617		4000	_	
	BC618		2000	_	
f <sub>T</sub>	transition frequency	I <sub>C</sub> = 500 mA; V <sub>CE</sub> = 5 V; f = 100 MHz	155	_	MHz

### NPN Darlington transistors

BC617; BC618

### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter			
	BC617		_	50	V
	BC618		_	80	V
V <sub>CES</sub>	collector-emitter voltage	V <sub>BE</sub> = 0			
	BC617		_	40	V
	BC618		_	55	V
V <sub>EBO</sub>	emitter-base voltage	open collector	_	12	V
I <sub>C</sub>	collector current (DC)		_	500	mA
I <sub>CM</sub>	peak collector current		_	800	mA
I <sub>B</sub>	base current (DC)		_	200	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	_	500	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C

#### Note

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	note 1	250	K/W

### Note

1. Transistor mounted on an FR4 printed-circuit board.

<sup>1.</sup> Transistor mounted on an FR4 printed-circuit board.

### NPN Darlington transistors

BC617; BC618

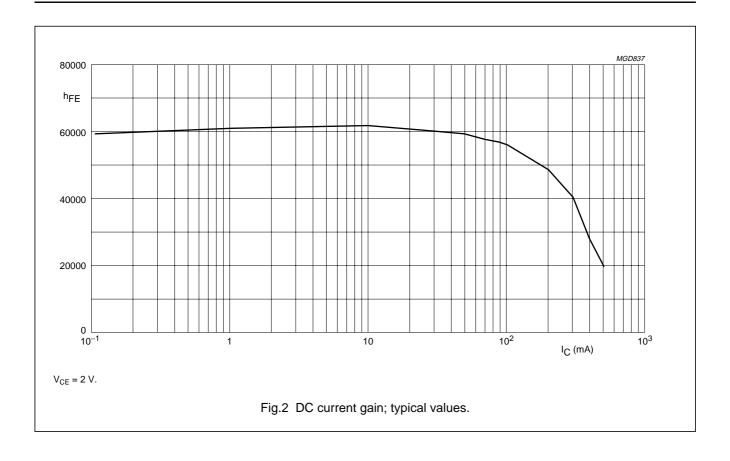
### **CHARACTERISTICS**

 $T_j = 25$  °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>CBO</sub>	collector cut-off current					
	BC617	I <sub>E</sub> = 0; V <sub>CB</sub> = 40 V	_	_	50	nA
	BC618	I <sub>E</sub> = 0; V <sub>CB</sub> = 60 V	_	_	50	nA
I <sub>CES</sub>	collector cut-off current					
	BC617	$V_{BE} = 0; V_{CE} = 40 \text{ V}$	_	_	50	μΑ
	BC618	V <sub>BE</sub> = 0; V <sub>CE</sub> = 60 V	_	_	50	μΑ
I <sub>EBO</sub>	emitter cut-off current	I <sub>C</sub> = 0; V <sub>EB</sub> = 10 V	_	_	50	nA
h <sub>FE</sub>	DC current gain	$I_C = 1 \text{ mA}$ ; $V_{CE} = 5 \text{ V}$ ; see Fig.2		_		
	BC617		4000	_	_	
	BC618		2000	_	_	
h <sub>FE</sub>	DC current gain	$I_C = 10 \text{ mA}$ ; $V_{CE} = 5 \text{ V}$ ; see Fig.2		_		
	BC617		10000	_	_	
	BC618		4000	_	_	
h <sub>FE</sub>	DC current gain	$I_C = 200 \text{ mA}$ ; $V_{CE} = 5 \text{ V}$ ; see Fig.2	10000	_	70000	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 200 \text{ mA}; I_B = 0.2 \text{ mA}$	_	_	1.1	V
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C = 200 \text{ mA}; I_B = 0.2 \text{ mA}$		_	1.6	V
C <sub>c</sub>	collector capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 30 V	_	3.5	_	pF
f <sub>T</sub>	transition frequency	$I_C = 500 \text{ mA}; V_{CE} = 5 \text{ V}; f = 100 \text{ MHz}$	155	_	_	MHz

### NPN Darlington transistors

BC617; BC618



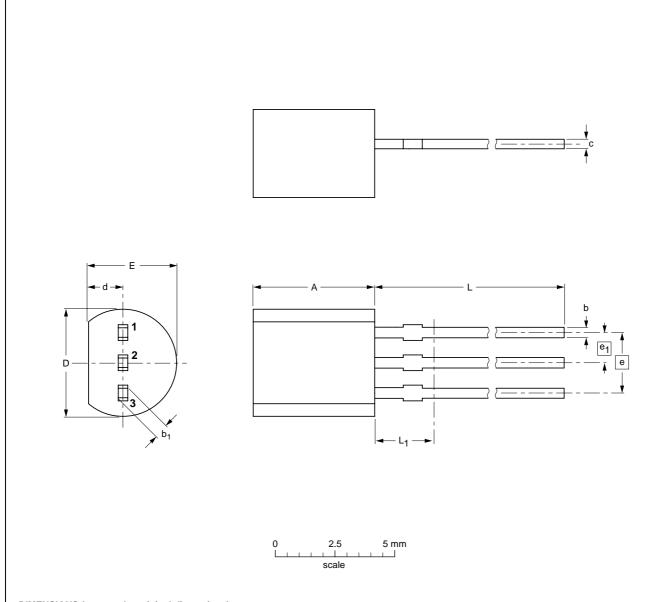
### NPN Darlington transistors

BC617; BC618

### **PACKAGE OUTLINE**

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



### DIMENSIONS (mm are the original dimensions)

UNIT	A	b	b <sub>1</sub>	С	D	d	E	е	e <sub>1</sub>	L	L <sub>1</sub> <sup>(1)</sup>
mm	5.2 5.0	0.48 0.40	0.66 0.56	0.45 0.40	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

#### Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE		REFER	REFERENCES			ISSUE DATE
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT54		TO-92	SC-43			97-02-28

### NPN Darlington transistors

BC617; BC618

#### **DEFINITIONS**

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	

Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

#### **Application information**

Where application information is given, it is advisory and does not form part of the specification.

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